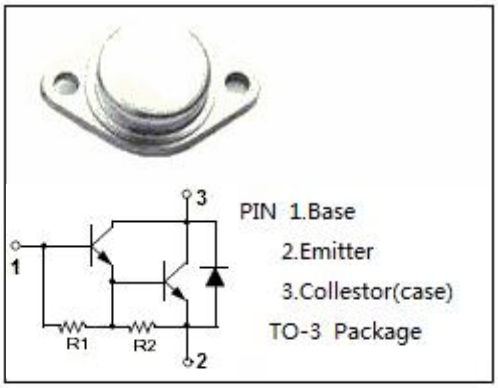
isc Silicon NPN Darlington Power Transistor 2SD920

DESCRIPTION

- High DC Current Gain
  : h_{FE}= 700(Min.)@ I_C= 1A, V_{CE}= 4V
- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$ = 200V(Min)
- Low Collector Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

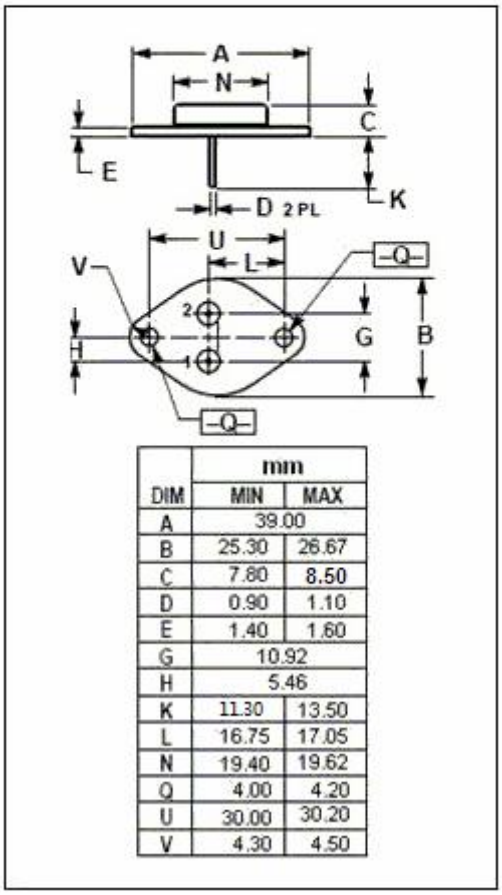


APPLICATIONS

- Designed for series regulators ,color TV, power supplies and similar devices applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	200	V
V_{CEO}	Collector-Emitter Voltage	200	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	8	A
P_C	Collector Power Dissipation @T_C=25℃	100	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 30mA, I_B= 0	200			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 3A ,I_B= 12mA			2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation voltage	I_C= 5A ,I_B= 20mA			4.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 3.0A ; V_{CE}= 3V			2.5	V
I_{CBO}	Collector Cutoff current	V_{CB}= 200V, I_E= 0			0.1	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= 200V, I_B= 0			0.5	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			5	mA
h_{FE}	DC Current Gain	I_C= 1A ; V_{CE}= 4V	700		20000	